

2N4410

NPN SILICON TRANSISTOR



TO-92 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N4410 is a small signal NPN silicon transistor, manufactured by the epitaxial planar process, designed for general purpose amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	250	mA
Power Dissipation	P_D	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	200	$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=100\text{V}$		10	nA
I_{CBO}	$V_{CB}=100\text{V}, T_A=100^\circ\text{C}$		1.0	μA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=10\mu\text{A}$	120		V
BV_{CEX}	$V_{BE}=5.0\text{V}, I_C=500\mu\text{A}, R_{BE}=8.2\text{k}\Omega$	120		V
BV_{CEO}	$I_C=1.0\text{mA}$	80		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		200	mV
$V_{BE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		800	mV
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$		800	mV
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	60		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	60	400	
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=20\text{MHz}$	60	300	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		12	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		50	pF

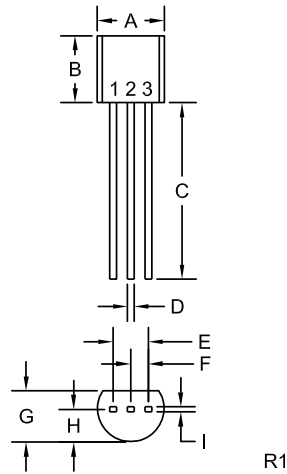
R0 (18-October 2010)

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TO-92 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:

FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R0 (18-October 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

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